

# BAT15-04R

## Reverse series silicon RF Schottky diode pair

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### Product description

These Infineon RF Schottky diodes are silicon low barrier N-type devices with an integrated guard ring on-chip for over-voltage protection. Their low barrier height, low forward voltage and low junction capacitance make BAT15-04R a suitable choice for mixer and detector functions in applications which frequencies are as high as 12 GHz.



### Feature list

- Low inductance  $L_S = 1.5$  nH (typical)
- Low capacitance  $C = 0.27$  pF (typical) at 1 MHz
- Industry standard SOT23-3 package (2.9 mm x 2.4 mm x 1 mm)
- Pb-free, RoHS compliant and halogen-free

### Product validation

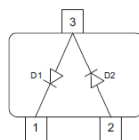
Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

### Potential applications

For mixers and detectors in:

- Satellite systems
- Low noise blocks for Ku bands
- Security systems

### Device information



**Table 1** Part information

Product name / Ordering code	Package	Pin configuration	Marking	Pieces / Reel
BAT15-04R / BAT1504RE6152HTSA1	SOT23-3	Reverse series pair	4R	3 k

**Attention:** *ESD (Electrostatic discharge) sensitive device, observe handling precautions!*

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**1 Absolute maximum ratings**

**Table 2 Absolute maximum ratings at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Diode reverse voltage	$V_R$	-	4	V	
Forward current	$I_F$	-	110	mA	
Total power dissipation	$P_{TOT}$	-	100	mW	$T_S \leq 77\text{ }^\circ\text{C}$ <sup>1)</sup>
Junction temperature	$T_J$	-	150	$^\circ\text{C}$	
Operating temperature	$T_{OP}$	-55	150		
Storage temperature	$T_{STG}$	-55	150		

**Attention:** *Stresses above the maximum values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Exceeding only one of these values may cause irreversible damage to the component.*

<sup>1</sup>  $T_S$  is the soldering point temperature.

**Electrical performance in test fixture**

**2 Electrical performance in test fixture**

**2.1 Electrical characteristics**

**Table 3 Electrical characteristics at  $T_A = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Breakdown voltage	$V_{BR}$	4	–	–	V	$I_R = 10\ \mu\text{A}$
Forward voltage	$V_F$	0.2	0.25	0.3	V	$I_F = 1\ \text{mA}$
		–	0.35	0.41		$I_F = 10\ \text{mA}$
Forward voltage matching	$\Delta V_F$	–	–	10	mV	$I_F = 1\ \text{mA}$ <sup>1)</sup>
Differential forward resistance	$R_F$	–	8	–	$\Omega$	$I_F = 10\ \text{mA} / 50\ \text{mA}$ <sup>2)</sup>
		–	12	18	$\Omega$	$I_F = 5\ \text{mA}$
Capacitance	$C$	–	0.26	0.3	pF	$V_R = 0\ \text{V}, f = 1\ \text{MHz}$
Inductance	$L_S$	–	1.5	–	nH	

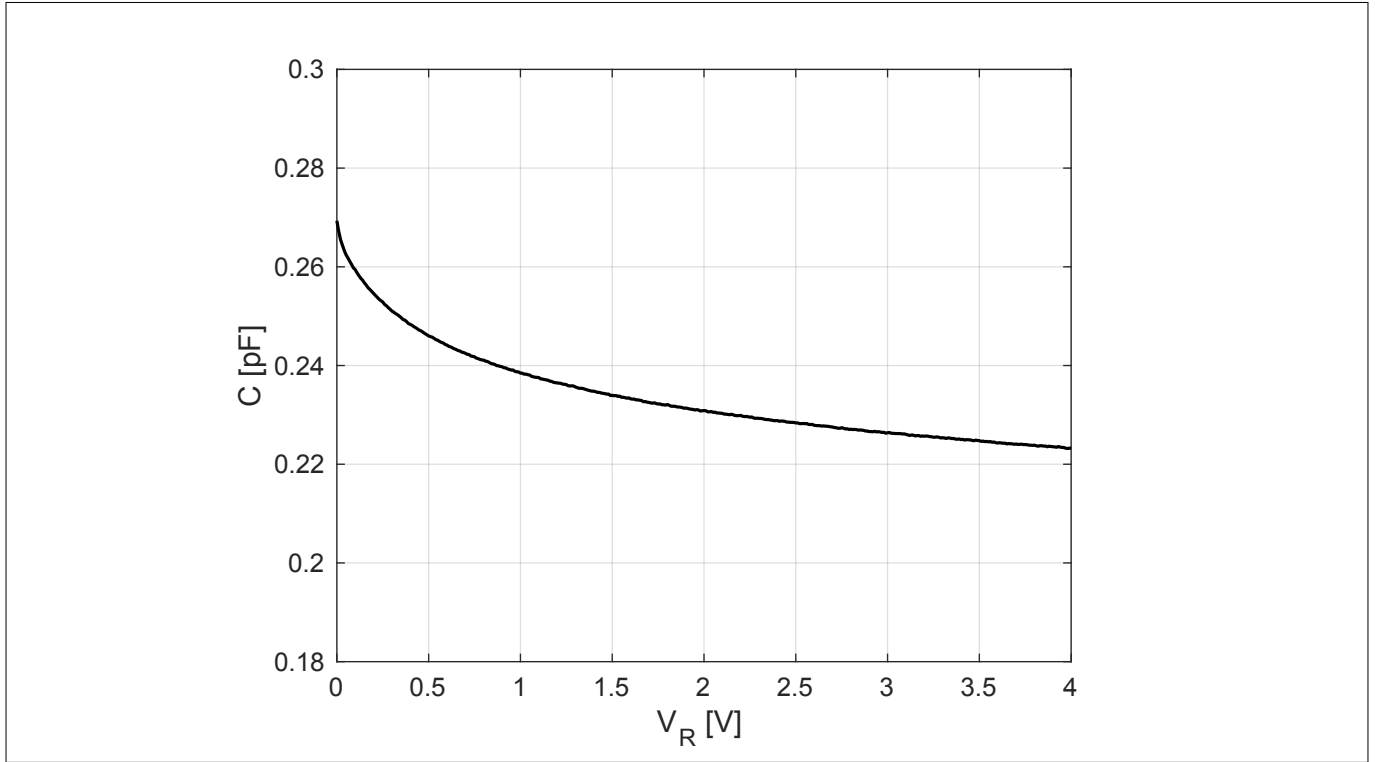
<sup>1</sup>  $\Delta V_F$  is the difference between lowest and highest  $V_F$  in a multiple diode component.

<sup>2</sup> 
$$R_F = \frac{V_F(50\ \text{mA}) - V_F(10\ \text{mA})}{50\ \text{mA} - 10\ \text{mA}}$$

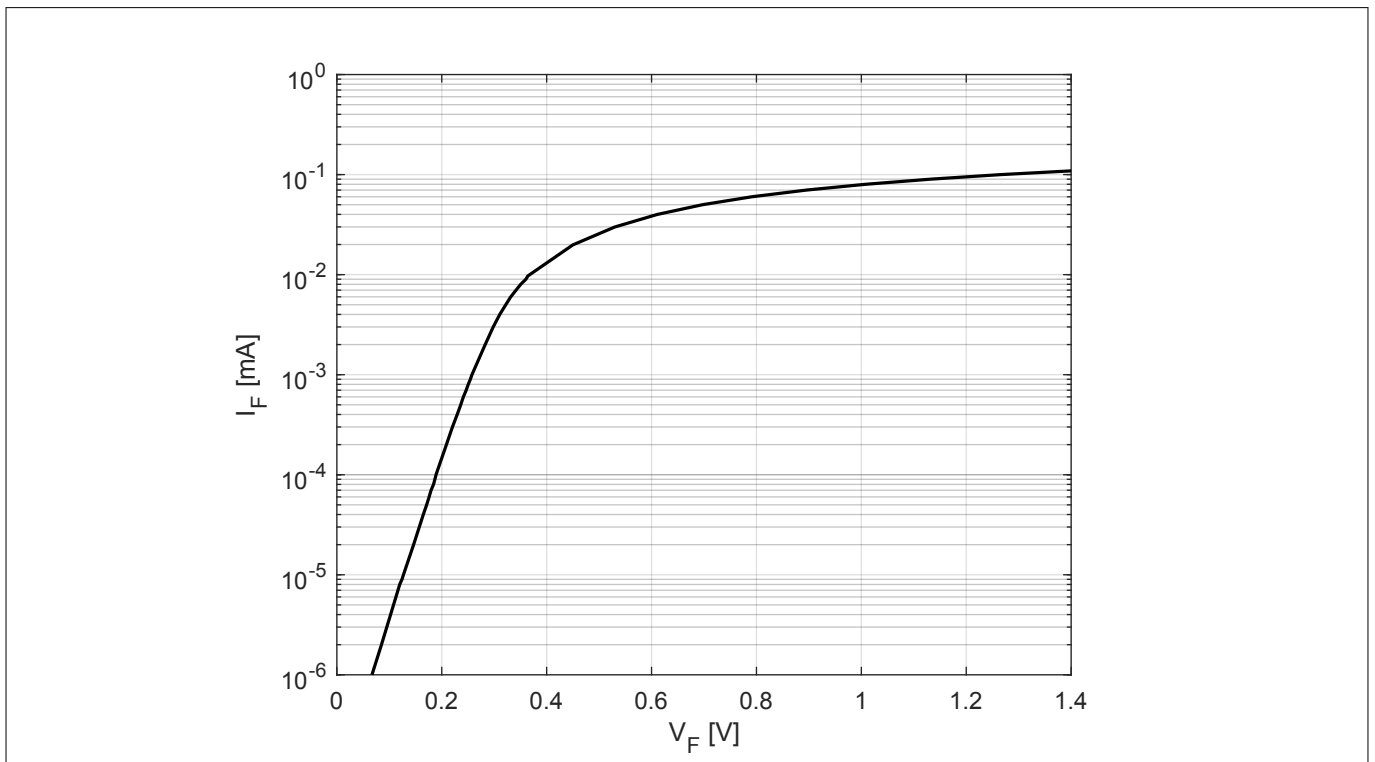
**Electrical performance in test fixture**

**2.2 Characteristic curves**

At  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified

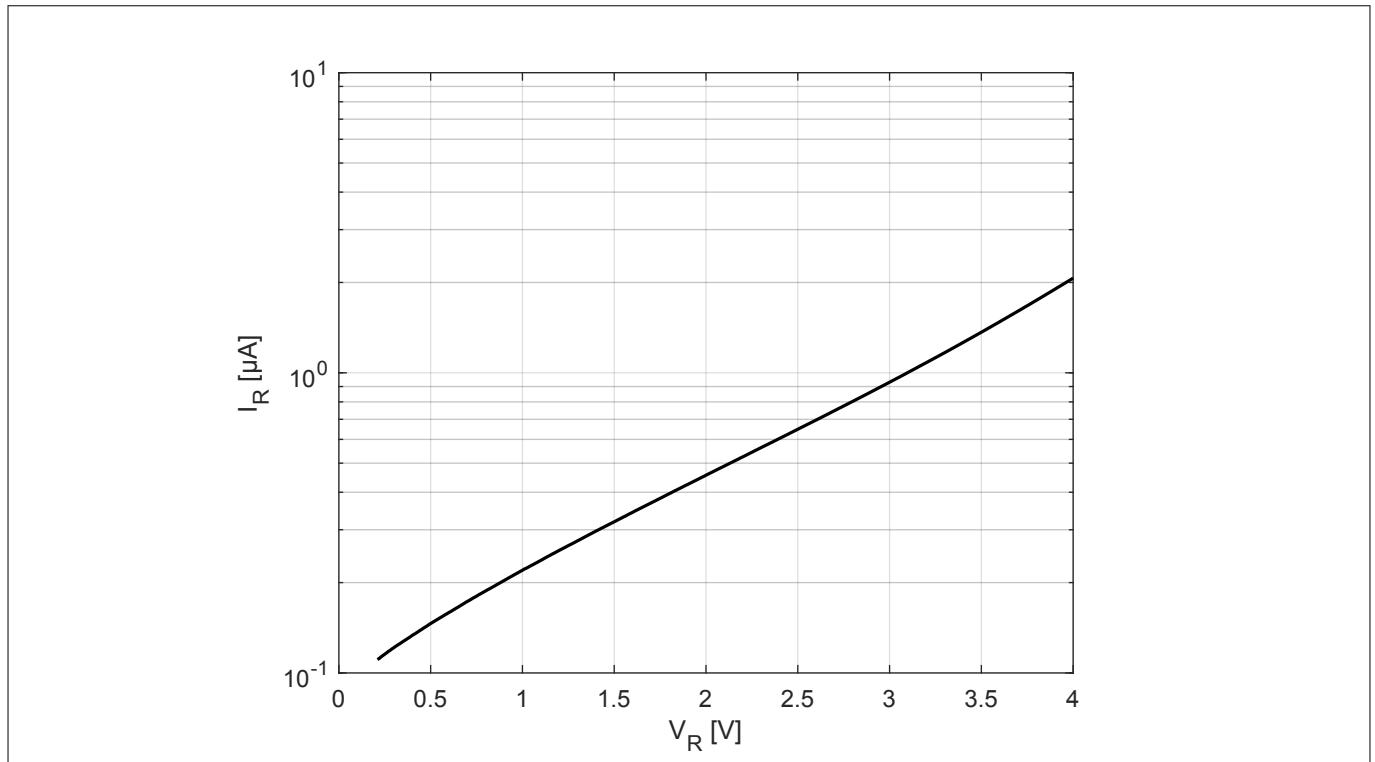


**Figure 1** Diode capacitance  $C$  vs. reverse voltage  $V_R$  at frequency  $f = 1\text{ MHz}$



**Figure 2** Forward current  $I_F$  vs. forward voltage  $V_F$

**Electrical performance in test fixture**



**Figure 3** Reverse current  $I_R$  vs. reverse voltage  $V_R$

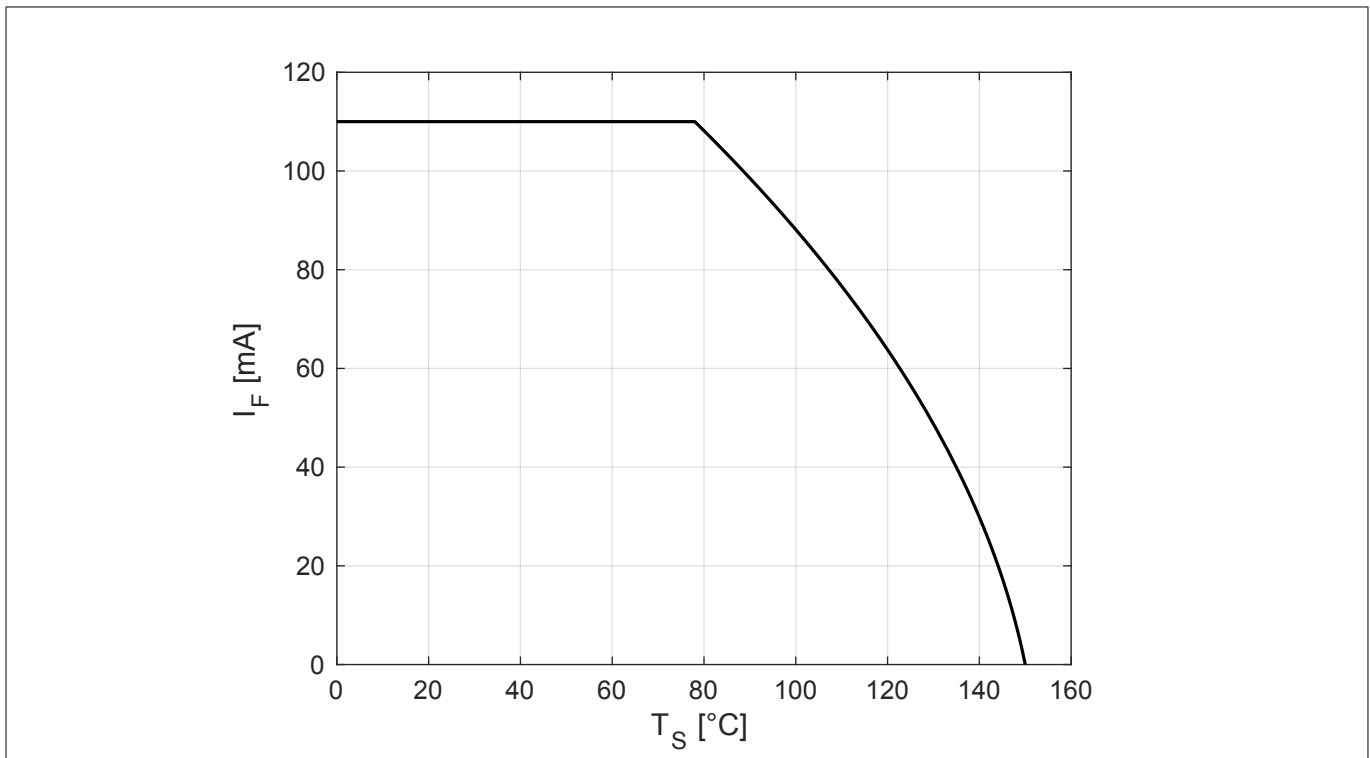
*Note:* The curves shown in this chapter have been generated using typical devices but shall not be understood as a guarantee that all devices have identical characteristic curves.

Thermal characteristics

### 3 Thermal characteristics

**Table 4 Thermal resistance**

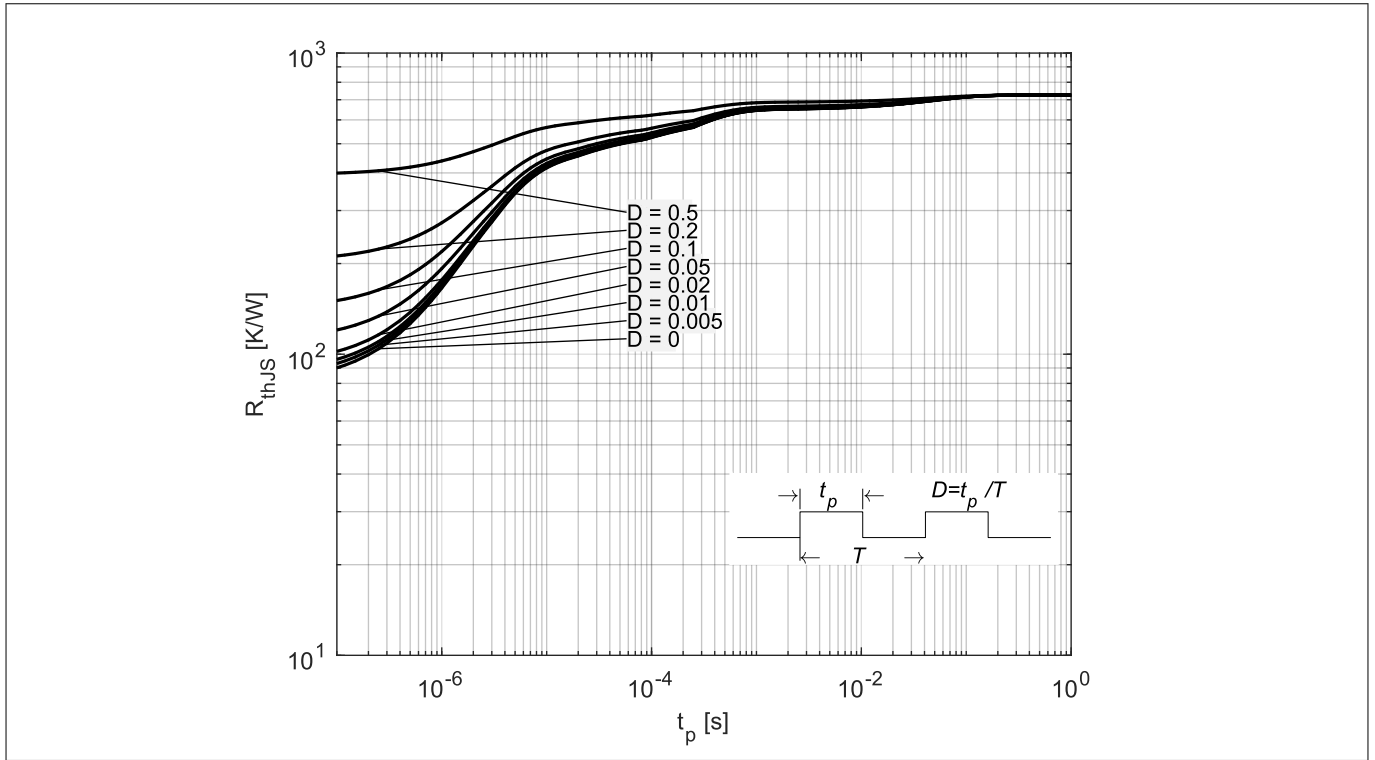
Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Thermal resistance (junction - soldering point)	$R_{thJS}$	-	725	-	K/W	$T_S = 77\text{ °C}$ <sup>1)</sup>



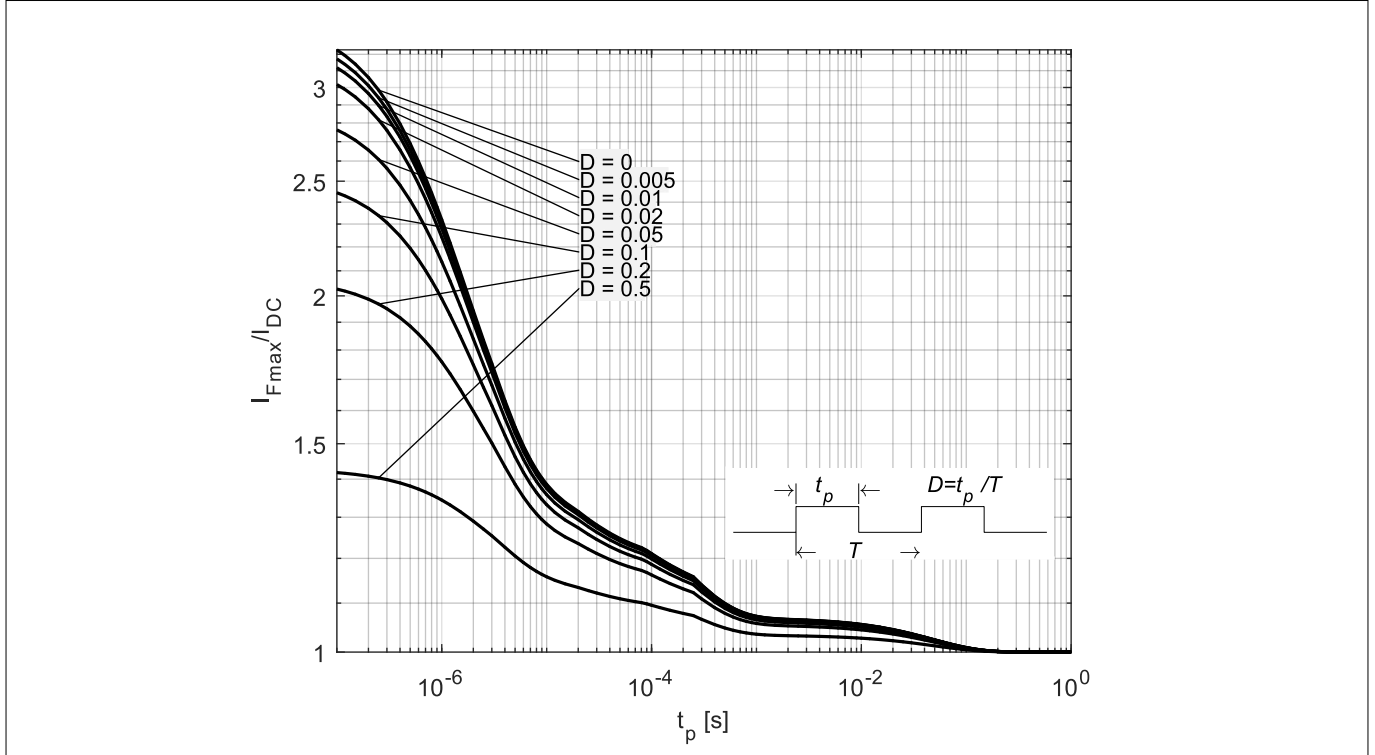
**Figure 4 Permissible forward current  $I_F$  in DC operation**

<sup>1</sup> For  $R_{thJS}$  in other conditions refer to the curves in this chapter.

**Thermal characteristics**



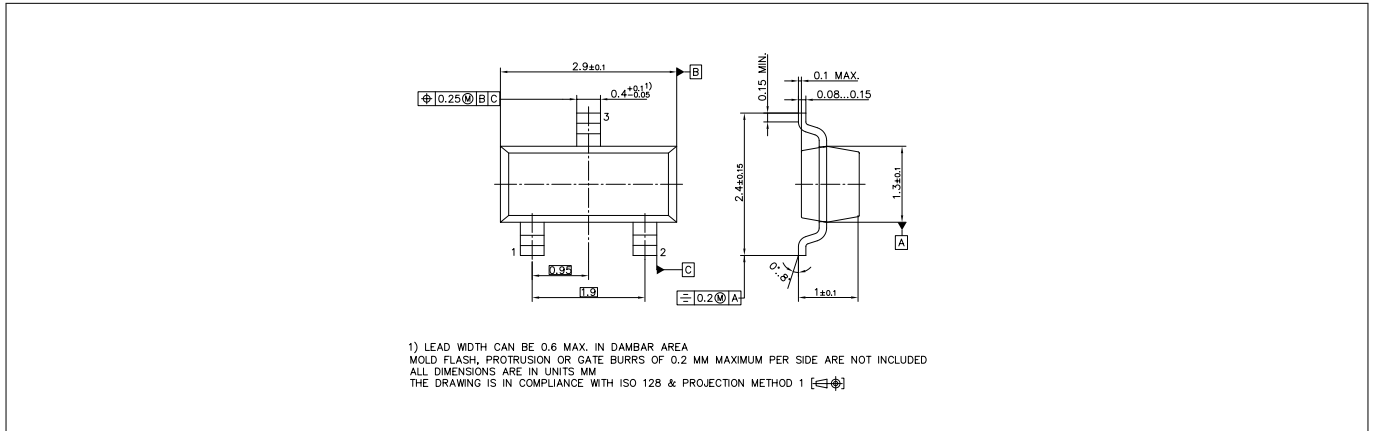
**Figure 5 Thermal resistance  $R_{thJS}$  in pulse operation**



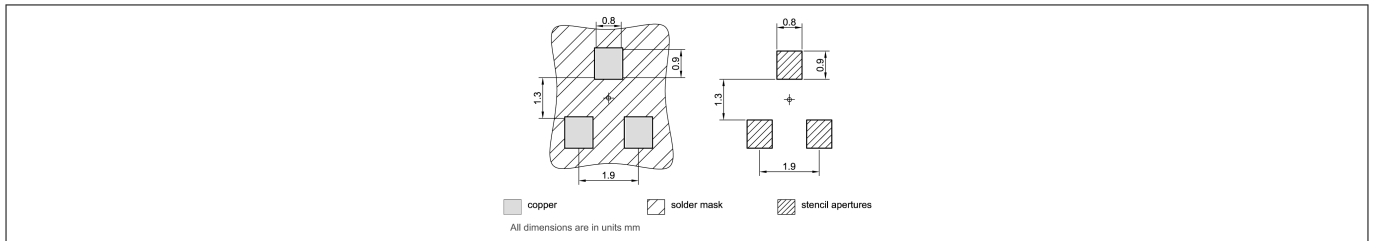
**Figure 6 Permissible forward current ratio  $I_{Fmax}/I_{DC}$  in pulse operation**

**Package information SOT23-3**

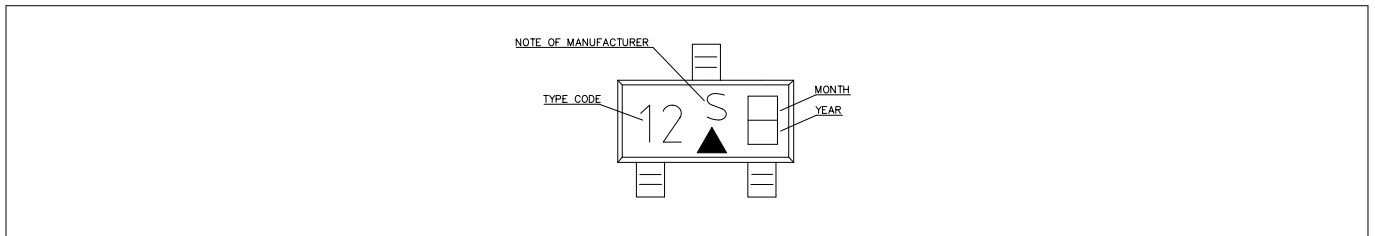
**4 Package information SOT23-3**



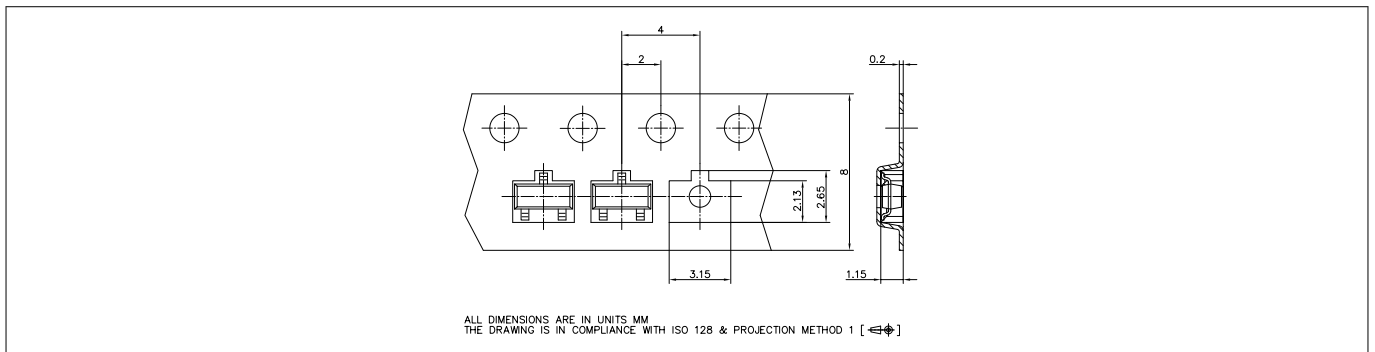
**Figure 7 Package outline**



**Figure 8 Foot print**



**Figure 9 Marking layout example**



**Figure 10 Tape dimensions**



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Revision history

## Revision history

Document version	Date of release	Description of changes
2.0	2018-09-28	<ul style="list-style-type: none"><li>• New layout of datasheet</li><li>• Typical values and curves updated to the values of the production (No product or process change behind)</li><li>• Maximum/typical values added</li></ul>

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